

Form PTO-1449		ATTORNEY DOCKET NO. 10003976-4	SERIAL NO. TBA
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		APPLICANT Moll et al.	
(Use several sheets if necessary)		FILING DATE TBA	GROUP TBA

REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS	
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME
D	AA 6,388,307	05/14/02	Kondo et al.
	AB 2002/0027232 A1	03/07/02	Shigematsu et al.
	AC 6,339,233	01/15/02	Lell
	AD 6,316,795	11/13/01	Croke, III
	AE 6,251,738	06/26/01	Huang
	AF 5,387,808	02/07/95	Nozu
V	AG 5,349,201	09/20/94	Stanchina et al.
D	AH 4,821,082	04/11/89	Frank et al.

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	TRANSLATION YES NO
v F	BA	EPO-0571994A2	05/27/93	Stanchina, William E.	X
	BB	JP-6-224230	08/12/94	Yashiki et al.	X
D	BC	WO 01/09957 A1	02/08/01	Micovic, Miroslav	X

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

OF	CA	Bell Telephone Laboratories, Inc., Semiconductor Device, Physics and Technology, S.M. SZE, AT&T Bell Laboratories, 1985, (267-269)
	CB	G.J. Sullivan, et al., MBE Growth and Characterization of High Gain AlGaAs/GaAsSb/GaAs NpN HBTs, Inst. Phys. Conf. Ser. No. 120: Chapter 13, 1991 (647-650)
	CC	N. Matine, et al., Electrical Stress Damage Reversed in Non-Passivated Fully Self-Aligned InP HBTs By Ozone Surface Treatment, Electronics Letters, December 9, 1999, Vol. 35, No. 25
	CD	C.R. Bolognesi, et al., High Performance InP/GaAsSb/InP DHBTs With Heavily Doped Base Layers, 2000 IEEE, (12-18)
	CE	S.P. Watkins, et al., Heavily Carbon-Doped GaAsSb Grown on InP For HBT Applications, Journal of Crystal Growth 221 (2000) (59-65)
	CF	M.W. Dvorak, et al. Abrupt Junction InP/GaAsSb/InP Double Heterojunction Bipolar Transistors With F_T as High As 250 GHz and $BV_{CEO} > 6V$, 2000 IEEE (178-181)
	CG	Tohru Oka, et al. Low Turn-on Voltage GaAs Heterojunction Bipolar Transistors With a Pseudomorphic GaAsSb Base, Applied Physics Letters, Vol 78, No. 4, 2001, (483485)
OF	CH	M.W. Dvorak, et al., MOCVD-Grown 175 GHz InP/GaAs _x Sb _{1-x} /InP DHBTs With High Current Gains Using Strained and Heavily C-Doped Base Layers

EXAMINER *Dashai* DATE CONSIDERED *5/16/06*

* Copies of these references are not enclosed Pursuant to 37 CFR 1.98(d). (See accompanying IDS)